

Delivering Modulation Solutions

NIR-MX-LN series

1000 nm band 10 GHz Intensity Modulator

Modulator



in the 1000 nm wavelength band.

The NIR-MX-LN-10 is an intensity modulator especially designed for operation

This Mach-Zehnder modulator offers engineers working at 1000 nm the intrinsic and unparalleled benefits of $LiNbO_3$ external modulation: high bandwidth, high contrast up to 30 dB and beyond, ease of use. Thanks to Photline Technologies proprietary waveguide process, the NIR-MX-LN-10 exhibits a stable behaviour and supports several tens mW of input optical power.

FEATURES

- Superior Extinction ratio : > 30 dB
- High Bandwidth (> 12 GHz)
- X-cut for high stability
- Low drive voltage
- Low insertion loss

APPLICATIONS

- Pulse generation / picking
- Carrier suppression
- Fiber optics sensors
- Pulse applications
- Analog transmission

OPTIONS

- 20 GHz version
- 1550 nm, 1300 nm band versions
- Choice of optical connectors

RELATED EQUIPMENTS

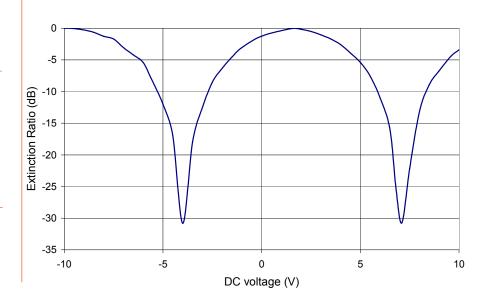
- RF amplifiers
- MBC-DG Automatic Bias Controllers

Performance Highlights

| Parameter | Min | Тур | Max | Unit |
|---------------------------|-----|-----|------|------|
| Operating wavelength | 980 | - | 1150 | nm |
| Insertion loss | - | 5 | - | dB |
| Extinction ratio | - | 30 | - | dB |
| Electro-optical bandwidth | - | 12 | - | GHz |
| Vπ RF @50 kHz | - | 4 | - | ٧ |
| Electrical return loss | - | 12 | - | dB |

Specifications given at 25 °C, 1060 nm

Extinction Ratio Response





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Electrical Characteristics

| Parameter | Symbol | Condition | Min | Тур | Max | Unit |
|-------------------------|------------------------|---------------------------|-----|-----|-----|------|
| Electro-optic bandwidth | S ₂₁ | RF electrodes, from 2 GHz | 10 | 12 | - | GHz |
| Ripple S21 | Δ\$21 | RF electrodes, f < 12GHz | - | 0.5 | 1 | dB |
| Electrical return loss | ES ₁₁ | RF electrodes | - | -12 | -10 | dB |
| Vπ RF @50 kHz | VπRF _{50 kHz} | RF electrodes | - | 4 | 4.5 | ٧ |
| Vπ DC electrodes | VπDC | DC electrodes | - | 5 | 6 | ٧ |
| RF input impedance | Z _{in-RF} | - | - | 40 | - | Ω |
| DC input impedance | Z _{in-DC} | - | - | 1 | - | MΩ |

Optical Characteristics All specifications given at 25°C, 1060 nm, unless differently specified

| Parameter | Symbol | Condition | Min | Тур | Max | Unit |
|----------------------|---------|--|------|---------------|-----------------|------|
| Crystal | - | - | | Lithium Nioba | te X-Cut Y-Prop | |
| Operating wavelength | λ | - | 980 | 1060 | 1150 | nm |
| Insertion loss | IL | Without connectors | - | 5 | 5.5 | dB |
| DC extinction ratio | ER > 20 | Measured with narrow source linewidth < 200 MHz | 20 | - | - | dB |
| | ER > 25 | | 25 | - | - | dB |
| | ER > 30 | | 30 | - | - | dB |
| Optical return loss | ORL | - | -40 | -45 | - | dB |
| Chirp | α | - | -0.1 | 0 | 0.1 | - |

Absolute Maximum Ratings

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. These are absolute stress ratings only. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of the data sheet. Exposure to absolute maximum ratings for extended periods can adversely affect device reliability.

| Parameter | Symbol | Min | Max | Unit |
|-----------------------|-------------------|-----|-----|------|
| RF input power | EP _{in} | - | 28 | dBm |
| Bias voltage | V _{bias} | -20 | +20 | V |
| Optical input power | OP _{in} | - | 20 | dBm |
| Operating temperature | ОТ | 0 | +70 | °C |
| Storage temperature | ST | -40 | +85 | °C |

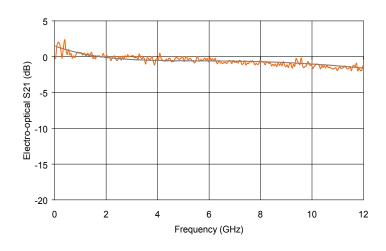


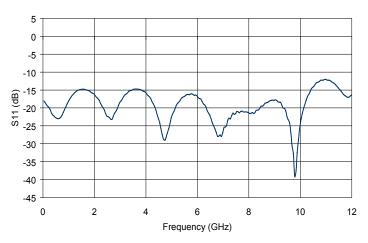
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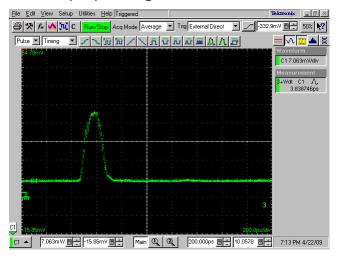
Modulator

S21 & S11 Parameter Curves at RF input port

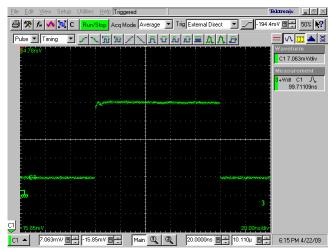




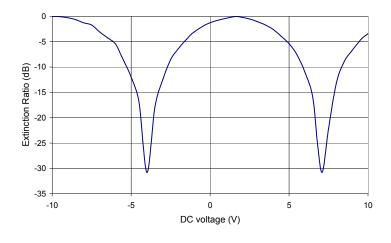
100 ps pulse generated



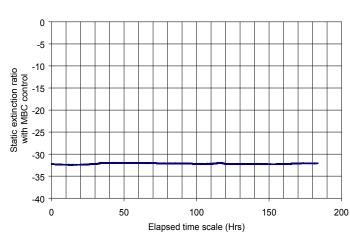
100 ns pulse generated



Extinction Ratio



Stability with Time and Temperature

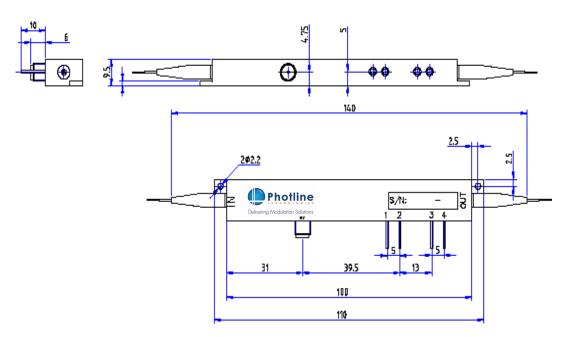




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Modulator

Mechanical Diagram and pinout All measurements in mm



| Port | Function | Note |
|------|---------------------|---|
| IN | Optical input port | Polarization maintaining fiber, Corning PM 98-U25A, Length 1.5 meter. Buffer diameter 900 μm |
| OUT | Optical output port | Polarization maintaining fiber, Corning PM 98-U25A, Length 1.5 meter. Buffer diameter 900 μm |
| RF | RF input port | Wiltron female K |
| 1 | Ground | Pin feed through diameter 1.0 mm |
| 2 | DC | Pin feed through diameter 1.0 mm |
| 3 | Photodiode cathode | Pin feed through diameter 1.0 mm |
| 4 | Photodiode anode | Pin feed through diameter 1.0 mm |

Ordering information

NIR-MX-LN-BW-XX-Y-Z-AB-CD-xxdB

BW = Bandwidth: 10 10 GHz 20 20 GHz

XX = Internal photodiode : 00 Not integrated PD PD Integrated Y = Input fiber : P Polarisation maintening S Standard single mode Z = Input fiber : P Polarisation maintening S Standard single mode AB = Output connector : 00 bare fiber FA FC/APC FC FC/SPC CD = Output connector : 00 bare fiber FA FC/APC FC FC/SPC

Note: optical connectors are Seikoh-Giken with narrow key or equivalent

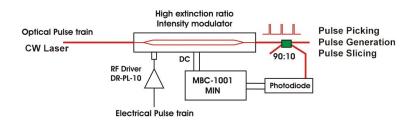
xxdB = Extinction ratio: 20 20 dB 25 25dB 30 30dB

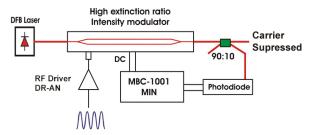


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Modulator

Related equipments





Pulse Generation / Picking / Slicing

Carrier suppressed / Analog modulation

DR-PL amplifiers series are intended to drive NIR-MX-LN as to generate undistorted optical pulses.



DR-AN amplifiers series are a wideband RF amplifiers modules designed for analog applications at frequencies up to 40 GHz.

MBC-DG-BT is an automatic bias controller designed to lock the operating point of the NIR-MX-LN modulators. MBC-DG-BT achieves an extinction ratio up to 50 dB with the proper modulator.



MBC-DG-BT is an automatic bias controller designed to lock the operating point of the NIR-MX-LN modulators.



Modbox-Pulse Modbxes are a family of turnkey optical transmitters and external benchtop units for pulse and other specific applications.

Pulse Genration / Pulse Picking / Slicing ModBoxes are Optical Modulation Units designed to generate controlled optical pulses.

About us

Photline Technologies is a provider of Fiber Optics Modulation Solutions based on the company LiNbO₃ modulators and high-speed electronics modules. Photline Technologies offers high speed and high data rate modulation solutions for the telecommunication industry and the defense, aerospace, instruments and sensors markets. The products offered by the company include: comprehensive range of intensity and phase modulators (800 nm, 1060 nm, 1300 nm, 1550 nm), RF drivers and modules, transmitters and modulation units.

ZI Les Tilleroyes - Trépillot 16, rue Auguste Jouchoux - 250000 Besançon - FRANCE tél. : +33 (0) 381 853 180 - fax : + 33 (0) 381 811 557 Pholline Technologies reserves the right to change, at any time and without notice, the specifications, design, function or form of its products described herein. All statements, specification, technical information related to the products herein are given in good faith and based upon information believed to be reliable and accurate at the moment of printing. However the accuracy and completeness thereof is not guaranteed. No liability is assumed for any inaccuracies and as a result of use of the products. The user must validate all parameters for each application before use and he assumes all risks in connection with the use of the products.